

## HeteroSiC & WASMPE 2013

Selected, peer reviewed papers from the 5th Edition of International Workshop on Silicon Carbide Hetero-Epitaxy and Workshop on Advanced Semiconductor Materials and Devices for Power Electronics Applications (HeteroSiC-WASMPE 2013), June 17-19, 2013, Nice

von  
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1. Auflage

Trans Tech Publications 2015

Verlag C.H. Beck im Internet:  
[www.beck.de](http://www.beck.de)

ISBN 978 3 03835 294 5

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